

Applic. No.: 10/666,228

Amdt. Dated December 30, 2005

Reply to Office action of October 4, 2005

REMARKS/ARGUMENTS

Reconsideration of the application is requested.

Claims 1, 5-6, and 9-13 are now in the application. Claims 1 and 6 have been amended. Claims 2-4 and 7-8 have been cancelled. Claims 9-13 have been added.

In item 2 on pages 2-3 of the above-mentioned Office action, claims 1, 3, and 5-6 have been rejected as being anticipated by Lanzerstorfer et al. (US 6,605,841 B2) under 35 U.S.C. § 102(e).

The rejection has been noted and claim 1 has been amended in an effort to even more clearly define the invention of the instant application. Support for the changes is found in Fig. 2 as well as on page 14, lines 9-14 of the specification. In addition, two independent claims 9 and 11 have been added, which correspond to the embodiments as shown in Figs. 1 and 3 respectively.

Before discussing the prior art in detail, it is believed that a brief review of the invention as claimed, would be helpful.

Claim 1 calls for, inter alia:

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a gate electrode disposed substantially between said body height and the semiconductor body surface, said gate electrode being electrically insulated from the semiconductor body by said gate oxide and having a lower edge with a profile, said profile having a horseshoe shape with two jaws projecting at edges thereof and a center between said jaws having an inward bulge in which said field electrode enters beyond said pn junction.

Claim 9 calls for, inter alia:

a gate electrode disposed substantially between said body height and the semiconductor body surface, said gate electrode being electrically insulated from the semiconductor body by said gate oxide and having a lower edge with a profile, said profile being at least partly obliquely angled relative to the semiconductor body surface, and said lower edge being provided above a top surface of said field electrode.

Claim 11 calls for, inter alia:

a gate electrode disposed substantially between said body height and the semiconductor body surface, said gate electrode being electrically insulated from the semiconductor body by said gate oxide and having a lower edge with a profile, said profile having a horseshoe shape with two jaws projecting at edges thereof and a center between said jaws having an inward bulge in which said field electrode enters, outer edges of said jaws being at least partly obliquely angled relative to the semiconductor body surface.

In Fig. 2H of Lanzerstorfer et al., the lower edge of the gate electrode 60A has a rounded profile. Clearly, Lanzerstorfer et al. do not show that the lower edge of the gate electrode has a profile "having a horseshoe shape with two jaws projecting at edges thereof and a center between said jaws having an inward bulge in which said field electrode enters beyond said pn junction", as recited in claim 1 of the instant

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application, "being at least partly obliquely angled relative to the semiconductor body surface, and said lower edge being provided above a top surface of said field electrode," as recited in claim 9 of the instant application, and "having a horseshoe shape with two jaws projecting at edges thereof and a center between said jaws having an inward bulge in which said field electrode enters, outer edges of said jaws being at least partly obliquely angled relative to the semiconductor body surface," as recited in claim 11 of the instant application.

Claims 1, 9, and 11 are, therefore, believed to be patentable over Lanzerstorfer et al. and since all of the dependent claims are dependent on claims 1, 9, and 11, they are believed to be patentable as well.

In view of the foregoing, reconsideration and allowance of claims 1, 5-6, and 9-13 are solicited.

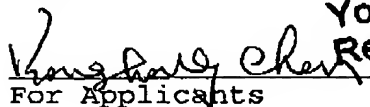
In the event the Examiner should still find any of the claims to be unpatentable, counsel would appreciate a telephone call so that, if possible, patentable language can be worked out.

If an extension of time for this paper is required, petition for extension is herewith made. Please charge any fees which

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might be due with respect to 37 CFR Sections 1.16 and 1.17 to
the Deposit Account of Lerner and Greenberg, P.A., No. 12-
1099.

Respectfully submitted,


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